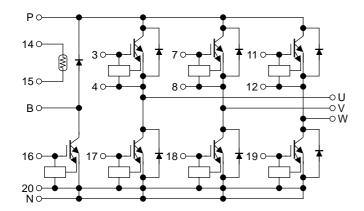
TOSHIBA GTR Module Silicon N Channel IGBT

# MG150J7KS60 (600V/150A 7in1)

## High Power Switching Applications Motor Control Applications

- Integrates inverter and brake power circuit into a single package
- The electrodes are isolated from case.
- Low thermal resistance
- $V_{CE (sat)} = 1.6 \text{ V (typ.)}$

#### **Equivalent Circuit**



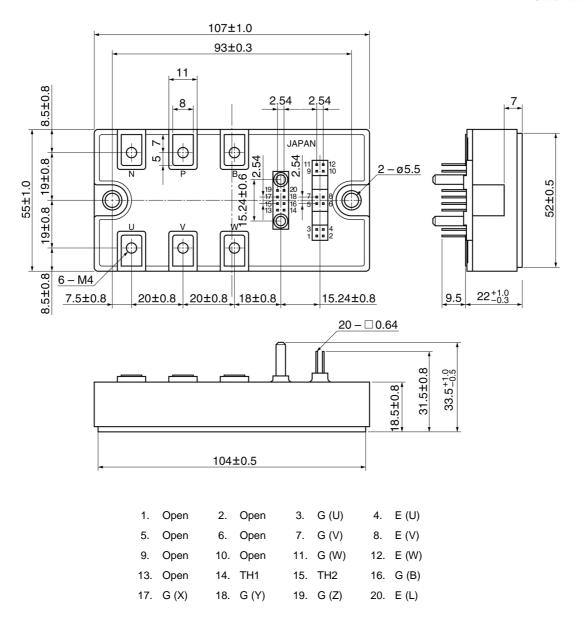
## **Signal Terminal**

1.	Open	2.	Open	3.	G (U)	4.	E (U)
5.	Open	6.	Open	7.	G (V)	8.	E (V)
9.	Open	10.	Open	11.	G (W)	12.	E (W)
13.	Open	14.	TH1	15.	TH2	16.	G (B)
17.	G (X)	18.	G (Y)	19.	G (Z)	20.	E(L)

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# Package Dimensions: 2-108G1B

Unit: mm



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## Maximum Ratings (Ta = 25°C)

Stage	Characteristics	Symbol	Rating	Unit		
	Collector-emitter voltage	V <sub>CES</sub>	600	V		
	Gate-emitter voltage	V <sub>GES</sub>	±20	V		
	Collector current	DC	Ic	150	Α	
Inverter	Collector current	1 ms	I <sub>CP</sub>	300	A	
	Forward current	DC	l <sub>F</sub>	150	۸	
	Forward current	1 ms	I <sub>FM</sub>	300	Α	
	Collector power dissipation (Tc =	PC	750	W		
	Collector-emitter voltage	V <sub>CES</sub>	600	V		
	Gate-emitter voltage	V <sub>GES</sub>	±20	V		
	Collector current	DC	Ic	75	Α	
Brake	Collector current	1 ms	I <sub>CP</sub>	150	A	
Diake	Collector power dissipation (Tc =	PC	375	W		
	Reverse voltage	V <sub>R</sub>	600	V		
	Forward current	DC	I <sub>F</sub>	75	Α	
	1 ms		I <sub>FM</sub>	150	A	
	Junction temperature	Tj	150	°C		
	Storage temperature range	T <sub>stg</sub>	-40~125	°C		
Module	Isolation voltage	V <sub>isol</sub>	2500 (AC 1 min)	V		
	Termin		_	2 (M4)	N·m	
	Screw torque	_	3 (M5)	IN.III		

# Electrical Characteristics ( $T_j = 25$ °C)

## 1. Inverter stage

Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$		_	_	±500	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0		_	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE</sub> (off)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 150 mA		5.0	6.5	8.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 150 A	$T_j = 25^{\circ}C$	_	1.6	2.2	V
				T <sub>j</sub> = 125°C	_	_	2.2	V
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz		_	25000	_	pF
	Turn-on delay time	t <sub>d (on)</sub>			_	_	1.00	
Switching time	Turn-off time	t <sub>off</sub>	$V_{CC} = 300 \text{ V}, I_{C} = 15 \text{ V}_{GE} = \pm 15 \text{ V}, R_{G} = 1$		_	_	1.20	
	Fall time	t <sub>f</sub>		(Note 1)	_	_	0.50	μS
Reverse recovery time		t <sub>rr</sub>			_	_	0.30	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 150 A		_	2.0	2.2	V

Note 1: Switching time test circuit & timing chart



## 2. Brake stage

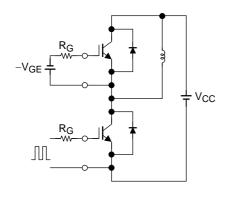
Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$		_	_	±500	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0		_	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE</sub> (off)	$V_{CE} = 5 \text{ V}, I_{C} = 75 \text{ mA}$		5.0	6.5	8.0	V
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 75 A	T <sub>j</sub> = 25°C	_	1.6	2.2	V
				$T_j = 125^{\circ}C$	_	_	2.2	
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1MHz		_	12000		pF
	Turn-on delay time	t <sub>d (on)</sub>	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 75 A		_	_	1.00	
Switching time	Turn-off time	t <sub>off</sub>	$V_{GE} = \pm 15 \text{ V, R}_{G} =$	= 24 Ω	_	_	1.20	μS
	Fall time	t <sub>f</sub>		(Note 1)	_	_	0.50	
Reverse current		I <sub>R</sub>	V <sub>R</sub> = 600 V		_	_	1.0	mA
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 75 A		_	2.1	2.6	V

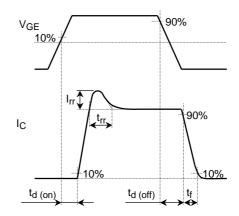
Note 1: Switching time test circuit & timing chart

#### 3. Module ( $Tc = 25^{\circ}C$ )

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Zero-power resistance R25 ITM = 0.2 mA		ITM = 0.2 mA	_	100	_	kΩ	
B value	B25/85 Tc = 25°C/Tc = 85°C		_	4390	_	K	
	В	Inverter IGBT stage	_	_	0.167		
Junction to case thermal resistance		Inverter FRD stage	_	_	0.313	°C/W	
Junction to case thermal resistance	R <sub>th (j-c)</sub>	Brake IGBT stage	_	_	0.333	C/VV	
		Brake FRD stage	_	_	1.000		
Case to fin thermal resistance	R <sub>th (c-f)</sub>	_	_	0.05	_	°C/W	

## **Switching Time Test Circuit & Timing Chart**





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